

**X2-Class HiPerFET™  
Power MOSFET**
**IXFK100N65X2  
IXFX100N65X2**

$$V_{DSS} = 650V$$

$$I_{D25} = 100A$$

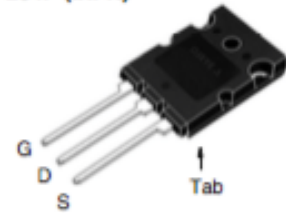
$$R_{DS(on)} \leq 30m\Omega$$

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

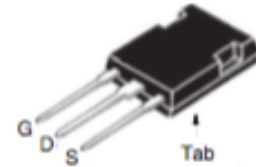


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	650	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	650	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	100	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	200	A
$I_A$	$T_C = 25^\circ C$	10	A
$E_{AS}$	$T_C = 25^\circ C$	3.5	J
$P_D$	$T_C = 25^\circ C$	1040	W
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DS} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	50	V/ns
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-264)	1.13/10	Nm/lb.in
$F_c$	Mounting Force (PLUS247)	20..120 / 4.5..27	N/lb
Weight	TO-264P	10	g
	PLUS247	6	g

TO-264P (IXFK)



PLUS247 (IXFX)



G = Gate      D = Drain  
S = Source    Tab = Drain

**Features**

- International Standard Packages
- Low  $Q_G$
- Avalanche Rated
- Low Package Inductance

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	650		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4mA$	2.7		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 5 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			30 m $\Omega$

Symbol	Test Conditions ( $T_j = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10V, I_D = 0.5 \cdot I_{DSS}$ , Note 1	40	68	S
$R_{GS}$	Gate Input Resistance		0.7	$\Omega$
$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1\text{MHz}$		11.3	nF
$C_{oss}$		6.0	nF	
$C_{rss}$		2.0	pF	
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{DSS}$ $R_D = 2\Omega$ (External)		59	ns
$t_r$		24	ns	
$t_{d(off)}$		83	ns	
$t_f$		7	ns	
$Q_{g(on)}$	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{DSS}$		180	nC
$Q_{gs}$		92	nC	
$Q_{gd}$		40	nC	
$R_{thJC}$			0.12	$^\circ\text{C/W}$
$R_{thCS}$		0.15	$^\circ\text{C/W}$	

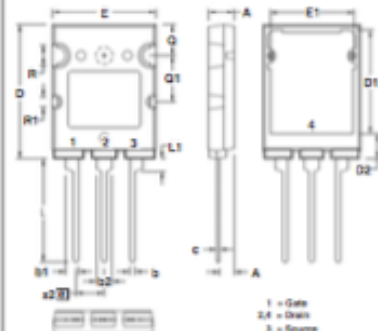
**Source-Drain Diode**

Symbol	Test Conditions ( $T_j = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0V$			100 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			400 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0V$ , Note 1			1.4 V
$t_{rr}$	$I_F = 50A, -di/dt = 100A/\mu\text{s}$ $V_R = 100V, V_{GS} = 0V$		205	ns
$Q_{RM}$		1.8	$\mu\text{C}$	
$I_{RM}$		18.0	A	

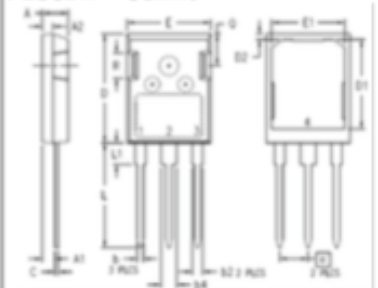
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

**TO-264P Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.30
A1	.102	.118	2.60	3.00
b	.035	.049	0.90	1.25
b1	.091	.106	2.30	2.70
b2	.110	.126	2.80	3.20
c	.020	.033	0.50	0.85
D	1.012	1.035	25.70	26.30
D1	.783	.799	19.90	20.30
D2	.185	.205	4.70	5.20
E	.776	.799	19.70	20.30
E1	.661	.677	16.80	17.20
e	.215 BSC		5.46 BSC	
L	.768	.807	19.50	20.50
L1	.091	.106	2.30	2.70
Q	.228	.244	5.80	6.20
Q1	.346	.362	8.80	9.20
Q2	.150	.165	3.80	4.20
QR1	.071	.087	1.80	2.20

**PLUS247™ Outline**


Terminals: 1 - Gate  
2,4 - Drain  
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
c	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.650	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.520	.560	13.08	14.22
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,308B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	